

# Saida Latreche

## List of Publications by Year in descending order

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29  
papers

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citations

1478505

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1281871

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docs citations

29  
times ranked

96  
citing authors

#	ARTICLE	IF	CITATIONS
1	Zirconium Complexes of Symmetric and of Chiral Diketiminato Ligands: Synthesis, Crystal Structures, and Reactivities. <i>Organometallics</i> , 2010, 29, 1551-1559.	2.3	27
2	Chromium(III) Bis(diketiminato) Complexes. <i>Organometallics</i> , 2010, 29, 2180-2185.	2.3	17
3	Compact drain-current model for undoped cylindrical surrounding-gate metal-oxide-semiconductor field effect transistors including short channel effects. <i>Journal of Applied Physics</i> , 2013, 114, .	2.5	17
4	Highly symmetrical chromium(II) bisdiketiminato complexes. <i>Inorganica Chimica Acta</i> , 2011, 365, 49-53.	2.4	11
5	Photonic band gap grating in He <sup>+</sup> -implanted lithium niobate waveguides. <i>Optical and Quantum Electronics</i> , 2007, 39, 333-340.	3.3	7
6	3,5-Bis(4-fluorophenyl)-1-propyl-1,3,5-triazacyclohexane. <i>Acta Crystallographica Section E: Structure Reports Online</i> , 2006, 62, o4674-o4675.	0.2	6
7	Mathematical approach and optimisation of nanometric base thickness for a SiGeC HBT dedicated to radiofrequency applications. <i>Journal of Computational and Applied Mathematics</i> , 2014, 259, 925-936.	2.0	6
8	3,5-Bis(2-fluorophenyl)-1-isopropyl-1,3,5-triazacyclohexane. <i>Acta Crystallographica Section E: Structure Reports Online</i> , 2006, 62, o4960-o4962.	0.2	5
9	1,3-Bis(2-fluorophenyl)-5-propyl-1,3,5-triazacyclohexane. <i>Acta Crystallographica Section E: Structure Reports Online</i> , 2006, 62, o4676-o4678.	0.2	4
10	Unsymmetrically substituted triazacyclohexanes and their chromium complexes. <i>Polyhedron</i> , 2010, 29, 1399-1404.	2.2	4
11	Experimentally verified drain-current model for variable barrier transistor. <i>Electronics Letters</i> , 2015, 51, 1364-1366.	1.0	4
12	Improvement of the Self-Heating Performance of an Advanced SiGe HBT Transistor Through the Peltier Effect. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 479-484.	3.0	3
13	Numerical modeling of MOS transistor with interconnections using lumped element-FDTD method. <i>Microelectronics Journal</i> , 2012, 43, 995-1002.	2.0	2
14	Analytical Drain-Current Model and Surface-Potential Calculation for Junctionless Cylindrical Surrounding-Gate MOSFETs. <i>International Journal of Circuits, Systems and Signal Processing</i> , 2021, 15, 1394-1399.	0.3	2
15	Compact border termination for active-edge planar radiation detectors with enhanced breakdown voltage. <i>Micro and Nano Letters</i> , 2020, 15, 969-971.	1.3	2
16	Mixed-mode analysis of the sensitivity of a radiofrequency oscillator disturbed by parasitic signals. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , 2009, 22, 23-42.	1.9	1
17	Numerical modeling of MOS transistor using implicit finite different-time domain method. , 2012, , .		1
18	Optimization of Abrupt Profile of Germanium in Si/SiGe Heterojunction Bipolar Transistor Specified for Radio Frequency Range Systems. <i>Applied Mechanics and Materials</i> , 2014, 492, 316-320.	0.2	1

#	ARTICLE	IF	CITATIONS
19	Compact Modeling of Lightly Doped Nanoscale DG MOSFET Transistor. Applied Mechanics and Materials, 2014, 492, 306-310.	0.2	1
20	UC1 Oscillator remotelab for distant electronics education. , 2014, , .		1
21	Numerical method for a 2D drift diffusion model arising in strained n-type MOSFET device. Pramana - Journal of Physics, 2016, 86, 1391-1400.	1.8	1
22	Nanoscale DGMOSFET: DC Modelisation and Analysis of Phase Noise in RF Oscillator. Journal of Applied Sciences, 2015, 15, 800-807.	0.3	1
23	Compact modeling of long channel Double Gate MOSFET transistor. , 2012, , .		0
24	A new approach of power electronic design using a nonlinear average model. COMPEL - the International Journal for Computation and Mathematics in Electrical and Electronic Engineering, 2012, 31, 1726-1756.	0.9	0
25	Static Performance of SiGe HBTs at Low Temperature. Applied Mechanics and Materials, 2014, 666, 59-63.	0.2	0
26	UC1 Oscillator Remote Lab for Distant Electronics Education. International Journal of Interactive Mobile Technologies, 2015, 9, 9.	1.2	0
27	Analytical Drain-Current Model and Surface-Potential Calculation for Junctionless Cylindrical Surrounding-Gate MOSFETs. International Journal of Circuits, Systems and Signal Processing, 2021, 15, 1585-1590.	0.3	0
28	COMSOL simulation of a new generation of SiGe heterojunction bipolar transistor (HBT) integrated in a BiCMOS 55nm technology. AIP Conference Proceedings, 2021, , .	0.4	0
29	The Analysis of the Polysilicon base Position of the Thermal Resistance and the Self Heating Effects of 0.13 $\mu\text{m}$ SiGe Heterojunction Bipolar Transistors. Russian Microelectronics, 2022, 51, 192-198.	0.5	0